AMD Xilinx - XC7K325T-2FF900I Datasheet

Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	25475
Number of Logic Elements/Cells	326080
Total RAM Bits	16404480
Number of I/O	500
Number of Gates	-
Voltage - Supply	0.97V ~ 1.03V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	900-BBGA, FCBGA
Supplier Device Package	900-FCBGA (31x31)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc7k325t-2ff900i

Table 2: **Recommended Operating Conditions (1) *(Cont'd)***

Symbol	Description	Min	Typ	Max	Units
$V_{MGTAVTTRCAL}$ (8)	Analog supply voltage for the resistor calibration circuit of the GTX transceiver column	1.17	1.2	1.23	V
XADC					
V_{CCADC}	XADC supply relative to GNDADC	1.71	1.80	1.89	V
V_{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V
Temperature					
T_j	Junction temperature operating range for commercial (C) temperature devices	0	–	85	°C
	Junction temperature operating range for extended (E) temperature devices	0	–	100	°C
	Junction temperature operating range for industrial (I) temperature devices	–40	–	100	°C

Notes:

1. All voltages are relative to ground.
2. V_{CCINT} and V_{CCBRAM} should be connected to the same supply.
3. Configuration data is retained even if V_{CCO} drops to 0V.
4. Includes V_{CCO} of 1.2V, 1.5V, 1.8V, 2.5V, and 3.3V.
5. The lower absolute voltage specification always applies.
6. A total of 200 mA per bank should not be exceeded.
7. V_{CCBATT} is required only when using bitstream encryption. If battery is not used, connect V_{CCBATT} to either ground or V_{CCAUX}.
8. Each voltage listed requires the filter circuit described in UG476: *7 Series FPGAs GTX/GTH Transceiver User Guide*.
9. For data rates ≤ 10.3125 Gb/s, $V_{MGTAVCC}$ should be 1.0V ±3% for lower power consumption.
10. For lower power consumption, $V_{MGTAVCC}$ should be 1.0V ±3% over the entire CPLL frequency range.

Table 3: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ(1)	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost)	0.75	–	–	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost)	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested)	–	–	15	µA
C_{IN} (2)	Die input capacitance at the pad	–	–	8	pF
I_{RPU}	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 3.3V	90	–	330	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 2.5V	68	–	250	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.8V	34	–	220	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.5V	23	–	150	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.2V	12	–	120	µA
I_{RPD}	Pad pull-down (when selected) @ V_{IN} = 3.3V	68	–	330	µA
	Pad pull-down (when selected) @ V_{IN} = 1.8V	45	–	180	µA
I_{CCADC}	Analog supply current, analog circuits in powered up state	–	–	25	mA
I_{BATT} (3)	Battery supply current	–	–	150	nA

Table 7 shows the minimum current, in addition to I_{CCQ}, that are required by Kintex-7 devices for proper power-on and configuration. If the current minimums shown in Table 6 and Table 7 are met, the device powers on after all five supplies have passed through their power-on reset threshold voltages. The FPGA must not be configured until after V_{CCINT} is applied.

Once initialized and configured, use the XPower tools to estimate current drain on these supplies.

Table 7: **Power-On Current for Kintex-7 Devices**

Device	$I_{CCINTMIN}$	$I_{CCAUXMIN}$	I_{CCOMIN}	I_{CCAUX_IOMIN}	$I_{CCBRAMMIN}$	Units
	Typ(1)	Typ(1)	Typ(1)	Typ(1)	Typ(1)	
XC7K70T	I_{CCINTQ} + 450	I_{CCAUXQ} + 40	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 40	mA
XC7K160T	I_{CCINTQ} + 550	I_{CCAUXQ} + 50	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 40	mA
XC7K325T	I_{CCINTQ} + 600	I_{CCAUXQ} + 80	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 40	mA
XC7K355T	I_{CCINTQ} + 1450	I_{CCAUXQ} + 109	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 81	mA
XC7K410T	I_{CCINTQ} + 1500	I_{CCAUXQ} + 125	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 90	mA
XC7K420T	I_{CCINTQ} + 2200	I_{CCAUXQ} + 180	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 108	mA
XC7K480T	I_{CCINTQ} + 2200	I_{CCAUXQ} + 180	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 108	mA

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. Use the XPower Estimator (XPE) spreadsheet tool (download at http://www.xilinx.com/power) to calculate maximum power-on currents.

Table 8: **Power Supply Ramp Time**

Symbol	Description	Conditions	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 90% of V_{CCINT}		0.2	50	ms
T_{VCCO}	Ramp time from GND to 90% of V_{CCO}		0.2	50	ms
T_{VCCAUX}	Ramp time from GND to 90% of V_{CCAUX}		0.2	50	ms
T_{VCCAUX_IO}	Ramp time from GND to 90% of V_{CCAUX_IO}		0.2	50	ms
$T_{VCCBRAM}$	Ramp time from GND to 90% of V_{CCBRAM}		0.2	50	ms
$T_{VCCO2VCCAUX}$	Allowed time per power cycle for $V_{CCO} - V_{CCAUX} > 2.625V$	T_J = 100°C(1)	–	500	ms
		T_J = 85°C(1)	–	800	
$T_{MGTAVCC}$	Ramp time from GND to 90% of $V_{MGTAVCC}$		0.2	50	ms
$T_{MGTAVTT}$	Ramp time from GND to 90% of $V_{MGTAVTT}$		0.2	50	ms
$T_{MGTVCCAUX}$	Ramp time from GND to 90% of $V_{MGTVCCAUX}$		0.2	50	ms

Notes:

1. Based on 240,000 power cycles with nominal V_{CCO} of 3.3V or 36,500 power cycles with a worst case V_{CCO} of 3.465V.

Table 10: **Differential SelectIO DC Input and Output Levels**

I/O Standard	V_{ICM}[1]			V_{ID}[2]			V_{OCM}[3]			V_{OD}[4]		
	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max
BLVDS_25	0.300	1.200	1.425	0.100	–	–	–	1.250	–	Note 5		
MINI_LVDS_25	0.300	1.200	V_{CCAUX}	0.200	0.400	0.600	1.000	1.200	1.400	0.300	0.450	0.600
PPDS_25	0.200	0.900	V_{CCAUX}	0.100	0.250	0.400	0.500	0.950	1.400	0.100	0.250	0.400
RSDS_25	0.300	0.900	1.500	0.100	0.350	0.600	1.000	1.200	1.400	0.100	0.350	0.600
TMDS_33	2.700	2.965	3.230	0.150	0.675	1.200	V_{CCO}–0.405	V_{CCO}–0.300	V_{CCO}–0.190	0.400	0.600	0.800

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage (Q – $\overline{Q}$).
3. V_{OCM} is the output common mode voltage.
4. V_{OD} is the output differential voltage (Q – $\overline{Q}$).
5. V_{OD} for BLVDS will vary significantly depending on topology and loading.
6. LVDS_25 is specified in Table 12.
7. LVDS is specified in Table 13.

Table 11: **Complementary Differential SelectIO DC Input and Output Levels**

I/O Standard	V_{ICM}[1]			V_{ID}[2]		V_{OL}[3]	V_{OH}[4]	I_{OL}	I_{OH}
	V, Min	V, Typ	V, Max	V, Min	V, Max	V, Max	V, Min	mA, Max	mA, Min
DIFF_HSTL_I	0.300	0.750	1.125	0.100	–	0.400	V_{CCO}–0.400	8.00	–8.00
DIFF_HSTL_I_18	0.300	0.900	1.425	0.100	–	0.400	V_{CCO}–0.400	8.00	–8.00
DIFF_HSTL_II	0.300	0.750	1.125	0.100	–	0.400	V_{CCO}–0.400	16.00	–16.00
DIFF_HSTL_II_18	0.300	0.900	1.425	0.100	–	0.400	V_{CCO}–0.400	16.00	–16.00
DIFF_HSUL_12	0.300	0.600	0.850	0.100	–	20% V_{CCO}	80% V_{CCO}	0.100	–0.100
DIFF_MOBILE_DDR	0.300	0.900	1.425	0.100	–	10% V_{CCO}	90% V_{CCO}	0.100	–0.100
DIFF_SSTL12	0.300	0.600	0.850	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	14.25	–14.25
DIFF_SSTL135	0.300	0.675	1.000	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	13.0	–13.0
DIFF_SSTL135_R	0.300	0.675	1.000	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	8.9	–8.9
DIFF_SSTL15	0.300	0.750	1.125	0.100	–	(V_{CCO}/2) – 0.175	(V_{CCO}/2) + 0.175	13.0	–13.0
DIFF_SSTL15_R	0.300	0.750	1.125	0.100	–	(V_{CCO}/2) – 0.175	(V_{CCO}/2) + 0.175	8.9	–8.9
DIFF_SSTL18_I	0.300	0.900	1.425	0.100	–	(V_{CCO}/2) – 0.470	(V_{CCO}/2) + 0.470	8.00	–8.00
DIFF_SSTL18_II	0.300	0.900	1.425	0.100	–	(V_{CCO}/2) – 0.600	(V_{CCO}/2) + 0.600	13.4	–13.4

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage (Q – $\overline{Q}$).
3. V_{OL} is the single-ended low-output voltage.
4. V_{OH} is the single-ended high-output voltage.

LVDS DC Specifications (LVDS_25)

The LVDS_25 standard is available in the HR I/O banks. See UG471: *7 Series FPGAs SelectIO Resources User Guide* for more information.

Table 12: **LVDS_25 DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		2.375	2.500	2.625	V
V_{OH}	Output High Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	–	–	1.675	V
V_{OL}	Output Low Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	0.700	–	–	V
V_{ODIFF}	Differential Output Voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	R_T = 100 Ω across Q and $\overline{Q}$ signals	247	350	600	mV
V_{OCM}	Output Common-Mode Voltage	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.000	1.250	1.425	V
V_{IDIFF}	Differential Input Voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High		100	350	600	mV
V_{ICM}	Input Common-Mode Voltage		0.300	1.200	1.425	V

LVDS DC Specifications (LVDS)

The LVDS standard is available in the HP I/O banks. See UG471: *7 Series FPGAs SelectIO Resources User Guide* for more information.

Table 13: **LVDS DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		1.710	1.800	1.890	V
V_{OH}	Output High Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	–	–	1.675	V
V_{OL}	Output Low Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	0.825	–	–	V
V_{ODIFF}	Differential Output Voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	R_T = 100 Ω across Q and $\overline{Q}$ signals	247	350	600	mV
V_{OCM}	Output Common-Mode Voltage	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.000	1.250	1.425	V
V_{IDIFF}	Differential Input Voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	Common-mode input voltage = 1.25V	100	350	600	mV
V_{ICM}	Input Common-Mode Voltage	Differential input voltage = ±350 mV	0.300	1.200	1.425	V

AC Switching Characteristics

All values represented in this data sheet are based on the speed specifications in ISE® software 14.3 v1.07 for the -3, -2, -2L(1.0V), -1, and v1.06 for -2L(0.9V) speed grades.

Switching characteristics are specified on a per-speed-grade basis and can be designated as Advance, Preliminary, or Production. Each designation is defined as follows:

Advance Product Specification

These specifications are based on simulations only and are typically available soon after device design specifications are frozen. Although speed grades with this designation are considered relatively stable and conservative, some under-reporting might still occur.

Preliminary Product Specification

These specifications are based on complete ES (engineering sample) silicon characterization. Devices and speed grades with this designation are intended to give a better indication of the expected performance of production silicon. The probability of under-reporting delays is greatly reduced as compared to Advance data.

Product Specification

These specifications are released once enough production silicon of a particular device family member has been characterized to provide full correlation between specifications and devices over numerous production lots. There is no under-reporting of delays, and customers receive formal notification of any subsequent changes. Typically, the slowest speed grades transition to production before faster speed grades.

Testing of AC Switching Characteristics

Internal timing parameters are derived from measuring internal test patterns. All AC switching characteristics are representative of worst-case supply voltage and junction temperature conditions.

For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer and back-annotate to the simulation net list. Unless otherwise noted, values apply to all Kintex-7 FPGAs.

Speed Grade Designations

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device. Table 14 correlates the current status of each Kintex-7 device on a per speed grade basis.

Table 14: **Kintex-7 Device Speed Grade Designations**

Device	Speed Grade Designations		
	Advance	Preliminary	Production
XC7K70T			-3, -2, -2L(1.0V), -1, and -2L (0.9V)
XC7K160T			-3, -2, -2L(1.0V), -1, and -2L (0.9V)
XC7K325T			-3, -2, -2L(1.0V), -1, and -2L (0.9V)
XC7K355T			-3, -2, -2L(1.0V), -1, and -2L (0.9V)
XC7K410T			-3, -2, -2L(1.0V), -1, and -2L (0.9V)
XC7K420T			-3, -2, -2L(1.0V), -1, and -2L (0.9V)
XC7K480T			-3, -2, -2L(1.0V), -1, and -2L (0.9V)

Production Silicon and ISE Software Status

In some cases, a particular family member (and speed grade) is released to production before a speed specification is released with the correct label (Advance, Preliminary, Production). Any labeling discrepancies are corrected in subsequent speed specification releases.

Table 15 lists the production released Kintex-7 device, speed grade, and the minimum corresponding supported speed specification version and ISE software revisions. The ISE software and speed specifications listed are the minimum releases required for production. All subsequent releases of software and speed specifications are valid.

Table 15: **Kintex-7 Device Production Software and Speed Specification Release**

Device	Speed Grade Designations			
	1.0V			0.9V
	-3	-2/-2L	-1	-2L
XC7K70T	ISE 14.2 v1.06			ISE 14.3 v1.06
XC7K160T	ISE 14.2 v1.06			ISE 14.3 v1.06
XC7K325T	ISE 14.2 v1.06			ISE 14.3 v1.06
XC7K355T	ISE 14.2 v1.06			ISE 14.3 v1.06
XC7K410T	ISE 14.2 v1.06			ISE 14.3 v1.06
XC7K420T	ISE 14.2 v1.06			ISE 14.3 v1.06
XC7K480T	ISE 14.2 v1.06			ISE 14.3 v1.06

Performance Characteristics

This section provides the performance characteristics of some common functions and designs implemented in Kintex-7 devices. The numbers reported here are worst-case values; they have all been fully characterized. These values are subject to the same guidelines as the AC Switching Characteristics, page 11. In each table, the I/O bank type is either High Performance (HP) or High Range (HR).

Table 16: **Networking Applications Interface Performances**

Description	I/O Bank Type	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
SDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 8)	HR	710	710	625	625	Mb/s
	HP	710	710	625	625	Mb/s
DDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 14)	HR	1250	1250	950	950	Mb/s
	HP	1600	1400	1250	1250	Mb/s
SDR LVDS receiver (SFI-4.1)(1)	HR	710	710	625	625	Mb/s
	HP	710	710	625	625	Mb/s
DDR LVDS receiver (SPI-4.2)(1)	HR	1250	1250	950	950	Mb/s
	HP	1600	1400	1250	1250	Mb/s

Notes:

1. LVDS receivers are typically bounded with certain applications where specific dynamic phase-alignment (DPA) algorithms dominate deterministic performance.

Table 18: **Maximum Physical Interface (PHY) Rate for Memory Interfaces (FBG Packages)(1)(2)**

Memory Standard	I/O Bank Type	V_{CCAUX_IO}(3)	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
4:1 Memory Controllers							
DDR3	HP	N/A	1333	1066	800	800	Mb/s
	HR	N/A	1066	800	800	800	Mb/s
DDR3L	HP	N/A	1066	800	667	667	Mb/s
	HR	N/A	800	800	667	667	Mb/s
DDR2	HP	N/A	800	800	800	800	Mb/s
	HR	N/A	800	667	667	667	Mb/s
RLDRAM III(4)	HP	N/A	550	500	450	450	MHz
	HR	N/A	N/A				
2:1 Memory Controllers							
DDR3	HP	N/A	1066	1066	800	800	Mb/s
	HR	N/A	1066	800	800	800	Mb/s
DDR3L	HP	N/A	1066	800	667	667	Mb/s
	HR	N/A	800	800	667	667	Mb/s
DDR2	HP	N/A	800	800	800	800	Mb/s
	HR	N/A	800	667	667	667	Mb/s
QDR II+(5)	HP	N/A	550	500	450	450	MHz
	HR	N/A	450	400	350	350	MHz
RLDRAM II	HP	N/A	533	500	450	450	MHz
	HR	N/A					
LPDDR2(4)	HP	N/A	667	667	667	667	Mb/s
	HR	N/A	667	667	533	533	Mb/s

Notes:

1. V_{REF} tracking is required. For more information, see UG586, *7 Series FPGAs Memory Interface Solutions User Guide*.
2. When using the internal V_{REF}, the maximum data rate is 800 Mb/s (400 MHz).
3. FBG packages do not have separate V_{CCAUX_IO} supply pins to adjust the pre-driver voltage of the HP I/O banks.
4. RLDRAM III (BL = 4, BL = 8) and LPDDR2 specifications have not been validated with memory IP.
5. The maximum QDRII+ performance specifications are for burst-length 4 (BL = 4) implementations. Burst length 2 (BL = 2) implementations are limited to 333 MHz for all speed grades and I/O bank types.

IOB Pad Input/Output/3-State

Table 19 (3.3V high-range IOB (HR)) and Table 20 (1.8V high-performance IOB (HP)) summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- T_{IOPI} is described as the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- T_{IOOP} is described as the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- T_{IOTP} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HP I/O banks, the internal DCI termination turn-on time is always faster than T_{IOTP} when the DCITERMDISABLE pin is used. In HR I/O banks, the IN_TERM termination turn-on time is always faster than T_{IOTP} when the INTERMDISABLE pin is used.

Table 19: **3.3V IOB High Range (HR) Switching Characteristics**

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
LVTTL_S4	1.31	1.42	1.64	1.51	5.27	5.63	6.05	4.13	6.03	6.49	7.04	4.64	ns
LVTTL_S8	1.31	1.42	1.64	1.51	4.45	4.83	5.30	3.86	5.21	5.69	6.29	4.38	ns
LVTTL_S12	1.31	1.42	1.64	1.51	4.45	4.83	5.29	3.84	5.21	5.69	6.28	4.36	ns
LVTTL_S16	1.31	1.42	1.64	1.51	3.47	3.88	4.40	3.39	4.23	4.74	5.39	3.91	ns
LVTTL_S24	1.31	1.42	1.64	1.51	3.58	3.99	4.51	3.61	4.34	4.85	5.50	4.13	ns
LVTTL_F4	1.31	1.42	1.64	1.51	4.70	4.98	5.29	3.58	5.46	5.84	6.28	4.09	ns
LVTTL_F8	1.31	1.42	1.64	1.51	3.66	4.06	4.56	3.06	4.42	4.92	5.55	3.58	ns
LVTTL_F12	1.31	1.42	1.64	1.51	3.66	4.06	4.56	3.05	4.42	4.92	5.55	3.56	ns
LVTTL_F16	1.31	1.42	1.64	1.51	2.57	2.85	3.15	2.88	3.33	3.71	4.14	3.39	ns
LVTTL_F24	1.31	1.42	1.64	1.51	2.41	2.64	2.89	2.94	3.17	3.50	3.88	3.45	ns
LVDS_25(1)	0.64	0.68	0.80	0.83	1.36	1.47	1.55	1.58	2.12	2.33	2.54	2.09	ns
MINI_LVDS_25	0.68	0.70	0.79	0.83	1.36	1.47	1.55	1.59	2.12	2.33	2.54	2.11	ns
BLVDS_25(1)	0.65	0.69	0.80	0.83	1.83	2.02	2.20	2.16	2.59	2.88	3.19	2.67	ns
RSDS_25 (point to point)(1)	0.63	0.68	0.79	0.83	1.36	1.48	1.55	1.59	2.12	2.34	2.54	2.11	ns
PPDS_25(1)	0.65	0.69	0.80	0.83	1.36	1.49	1.58	1.59	2.12	2.35	2.57	2.11	ns
TMDS_33(1)	0.72	0.76	0.86	0.83	1.43	1.54	1.60	1.70	2.19	2.40	2.59	2.22	ns
PCI33_3(1)	1.28	1.41	1.65	1.50	2.71	3.08	3.52	3.42	3.47	3.94	4.51	3.94	ns
HSUL_12	0.63	0.64	0.71	0.79	2.06	2.31	2.59	2.13	2.82	3.17	3.58	2.64	ns
DIFF_HSUL_12	0.58	0.61	0.70	0.81	1.83	2.04	2.26	1.92	2.59	2.90	3.25	2.44	ns
HSTL_I_S	0.61	0.64	0.73	0.79	1.55	1.69	1.80	1.91	2.31	2.55	2.79	2.42	ns
HSTL_II_S	0.61	0.64	0.73	0.78	1.21	1.34	1.43	1.70	1.97	2.20	2.42	2.22	ns
HSTL_I_18_S	0.64	0.67	0.76	0.79	1.28	1.39	1.45	1.58	2.04	2.25	2.44	2.09	ns
HSTL_II_18_S	0.64	0.67	0.76	0.79	1.18	1.31	1.40	1.69	1.94	2.17	2.39	2.20	ns
DIFF_HSTL_I_S	0.63	0.67	0.77	0.78	1.42	1.54	1.61	1.84	2.18	2.40	2.60	2.36	ns
DIFF_HSTL_II_S	0.63	0.67	0.77	0.79	1.15	1.24	1.27	1.78	1.91	2.10	2.26	2.30	ns
DIFF_HSTL_I_18_S	0.65	0.69	0.78	0.79	1.27	1.38	1.43	1.67	2.03	2.24	2.42	2.19	ns
DIFF_HSTL_II_18_S	0.65	0.69	0.78	0.81	1.14	1.23	1.26	1.72	1.90	2.09	2.25	2.23	ns

Table 19: **3.3V IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	1.0V			0.9V	1.0V			0.9V	1.0V			0.9V	
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	
LVCMOS15_S16	0.66	0.69	0.81	0.90	1.76	1.95	2.13	1.91	2.52	2.81	3.12	2.42	ns
LVCMOS15_F4	0.66	0.69	0.81	0.90	3.39	3.60	3.80	1.98	4.15	4.46	4.79	2.50	ns
LVCMOS15_F8	0.66	0.69	0.81	0.90	1.79	1.99	2.18	1.92	2.55	2.85	3.17	2.44	ns
LVCMOS15_F12	0.66	0.69	0.81	0.90	1.40	1.54	1.65	1.67	2.16	2.40	2.64	2.19	ns
LVCMOS15_F16	0.66	0.69	0.81	0.90	1.37	1.51	1.61	1.66	2.13	2.37	2.60	2.17	ns
LVCMOS12_S4	0.88	0.91	1.00	1.01	3.85	4.22	4.69	2.89	4.61	5.08	5.68	3.41	ns
LVCMOS12_S8	0.88	0.91	1.00	1.01	2.52	2.96	3.52	2.41	3.28	3.82	4.51	2.92	ns
LVCMOS12_S12(1)	0.88	0.91	1.00	1.01	2.06	2.31	2.59	2.11	2.82	3.17	3.58	2.63	ns
LVCMOS12_F4	0.88	0.91	1.00	1.01	3.44	3.73	4.06	2.30	4.20	4.59	5.05	2.81	ns
LVCMOS12_F8	0.88	0.91	1.00	1.01	1.72	2.04	2.40	1.86	2.48	2.90	3.39	2.38	ns
LVCMOS12_F12(1)	0.88	0.91	1.00	1.01	1.54	1.71	1.87	1.69	2.30	2.57	2.86	2.20	ns
SSTL135_S	0.61	0.64	0.73	0.79	1.27	1.40	1.50	1.64	2.03	2.26	2.49	2.16	ns
SSTL15_S	0.61	0.64	0.73	0.73	1.24	1.37	1.47	1.59	2.00	2.23	2.46	2.11	ns
SSTL18_I_S	0.64	0.67	0.76	0.79	1.59	1.74	1.85	1.95	2.35	2.60	2.84	2.47	ns
SSTL18_II_S	0.64	0.67	0.76	0.78	1.27	1.40	1.50	1.63	2.03	2.26	2.49	2.14	ns
DIFF_SSTL135_S	0.59	0.61	0.73	0.79	1.27	1.40	1.50	1.64	2.03	2.26	2.49	2.16	ns
DIFF_SSTL15_S	0.63	0.67	0.77	0.79	1.24	1.37	1.47	1.59	2.00	2.23	2.46	2.11	ns
DIFF_SSTL18_I_S	0.65	0.69	0.78	0.79	1.50	1.63	1.72	1.95	2.26	2.49	2.71	2.47	ns
DIFF_SSTL18_II_S	0.65	0.69	0.78	0.79	1.13	1.22	1.25	1.66	1.89	2.08	2.24	2.17	ns
SSTL135_F	0.61	0.64	0.73	0.79	1.04	1.17	1.26	1.42	1.80	2.03	2.25	1.94	ns
SSTL15_F	0.61	0.64	0.73	0.73	1.04	1.17	1.26	1.39	1.80	2.03	2.25	1.91	ns
SSTL18_I_F	0.64	0.67	0.76	0.79	1.12	1.22	1.26	1.44	1.88	2.08	2.25	1.95	ns
SSTL18_II_F	0.64	0.67	0.76	0.78	1.05	1.18	1.28	1.42	1.81	2.04	2.27	1.94	ns
DIFF_SSTL135_F	0.59	0.61	0.73	0.79	1.04	1.17	1.26	1.42	1.80	2.03	2.25	1.94	ns
DIFF_SSTL15_F	0.63	0.67	0.77	0.79	1.04	1.17	1.26	1.39	1.80	2.03	2.25	1.91	ns
DIFF_SSTL18_I_F	0.65	0.69	0.78	0.79	1.10	1.19	1.23	1.52	1.86	2.05	2.22	2.03	ns
DIFF_SSTL18_II_F	0.65	0.69	0.78	0.79	1.02	1.10	1.14	1.50	1.78	1.96	2.13	2.02	ns

Notes:

1. This I/O standard is only available in the 3.3V high-range (HR) banks.

Table 21 specifies the values of T_{IOTPHZ} and $T_{IOIBUFDISABLE}$. T_{IOTPHZ} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). $T_{IOIBUFDISABLE}$ is described as the IOB delay from IBUFDISABLE to O output. In HP I/O banks, the internal DCI termination turn-off time is always faster than T_{IOTPHZ} when the DCITERMDISABLE pin is used. In HR I/O banks, the internal IN_TERM termination turn-off time is always faster than T_{IOTPHZ} when the INTERMDISABLE pin is used.

Table 21: **IOB 3-state Output Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
T_{IOTPHZ}	T input to pad high-impedance	0.76	0.86	0.99	0.62	ns
$T_{IOIBUFDISABLE\_HR}$	IBUF turn-on time from IBUFDISABLE to O output for HR I/O banks	1.72	1.89	2.14	2.17	ns
$T_{IOIBUFDISABLE\_HP}$	IBUF turn-on time from IBUFDISABLE to O output for HP I/O banks	1.31	1.46	1.76	1.86	ns

Table 27: **IO_FIFO Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
IO_FIFO Clock to Out Delays						
T_{OFFCKO_DO}	RDCLK to Q outputs	0.51	0.56	0.63	0.81	ns
T_{CKO_FLAGS}	Clock to IO_FIFO Flags	0.59	0.62	0.81	0.77	ns
Setup/Hold						
T_{CCK_D}/T_{CKC_D}	D inputs to WRCLK	0.43/–0.01	0.47/–0.01	0.53/–0.01	0.76/–0.05	ns
$T_{IFFCCK\_WREN}/T_{IFFCKC\_WREN}$	WREN to WRCLK	0.39/–0.01	0.43/–0.01	0.50/–0.01	0.70/–0.05	ns
$T_{OFFCCK\_RDEN}/T_{OFFCKC\_RDEN}$	RDEN to RDCLK	0.49/0.01	0.53/0.02	0.61/0.02	0.79/–0.02	ns
Minimum Pulse Width						
$T_{PWH\_IO\_FIFO}$	RESET, RDCLK, WRCLK	0.81	0.92	1.08	1.29	ns
$T_{PWL\_IO\_FIFO}$	RESET, RDCLK, WRCLK	0.81	0.92	1.08	1.29	ns
Maximum Frequency						
F_{MAX}	RDCLK and WRCLK	533.05	470.37	400.00	333.33	MHz

Block RAM and FIFO Switching Characteristics

Table 31: **Block RAM and FIFO Switching Characteristics**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Block RAM and FIFO Clock-to-Out Delays						
T_{RCKO_DO} and $T_{RCKO\_DO\_REG}$[1]	Clock CLK to DOUT output (without output register)[2][3]	1.57	1.80	2.08	2.44	ns, Max
	Clock CLK to DOUT output (with output register)[4][5]	0.54	0.63	0.75	0.86	ns, Max
$T_{RCKO\_DO\_ECC}$ and $T_{RCKO\_DO\_ECC\_REG}$	Clock CLK to DOUT output with ECC (without output register)[2][3]	2.35	2.58	3.26	4.49	ns, Max
	Clock CLK to DOUT output with ECC (with output register)[4][5]	0.62	0.69	0.80	0.94	ns, Max
$T_{RCKO\_DO\_CASCOUT}$ and $T_{RCKO\_DO\_CASCOUT\_REG}$	Clock CLK to DOUT output with Cascade (without output register)[2]	2.21	2.45	2.80	3.19	ns, Max
	Clock CLK to DOUT output with Cascade (with output register)[4]	0.98	1.08	1.24	1.32	ns, Max
T_{RCKO_FLAGS}	Clock CLK to FIFO flags outputs[6]	0.65	0.74	0.89	0.97	ns, Max
$T_{RCKO\_POINTERS}$	Clock CLK to FIFO pointers outputs[7]	0.79	0.87	0.98	1.10	ns, Max
$T_{RCKO\_PARITY\_ECC}$	Clock CLK to ECCPARITY in ECC encode only mode	0.66	0.72	0.80	0.93	ns, Max
$T_{RCKO\_SDBIT\_ECC}$ and $T_{RCKO\_SDBIT\_ECC\_REG}$	Clock CLK to BITERR (without output register)	2.17	2.38	3.01	4.15	ns, Max
	Clock CLK to BITERR (with output register)	0.57	0.65	0.76	0.89	ns, Max
$T_{RCKO\_RDADDR\_ECC}$ and $T_{RCKO\_RDADDR\_ECC\_REG}$	Clock CLK to RDADDR output with ECC (without output register)	0.64	0.74	0.90	0.98	ns, Max
	Clock CLK to RDADDR output with ECC (with output register)	0.71	0.79	0.92	1.10	ns, Max
Setup and Hold Times Before/After Clock CLK						
$T_{RCCK\_ADDRA}/T_{RCKC\_ADDRA}$	ADDR inputs[8]	0.38/0.27	0.42/0.28	0.48/0.31	0.65/0.38	ns, Min
$T_{RDCK\_DI\_WF\_NC}/T_{RCKD\_DI\_WF\_NC}$	Data input setup/hold time when block RAM is configured in WRITE_FIRST or NO_CHANGE mode[9]	0.49/0.51	0.55/0.53	0.63/0.57	0.78/0.64	ns, Min
$T_{RDCK\_DI\_RF}/T_{RCKD\_DI\_RF}$	Data input setup/hold time when block RAM is configured in READ_FIRST mode[9]	0.17/0.25	0.19/0.29	0.21/0.35	0.25/0.32	ns, Min
$T_{RDCK\_DI\_ECC}/T_{RCKD\_DI\_ECC}$	DIN inputs with block RAM ECC in standard mode[9]	0.42/0.37	0.47/0.39	0.53/0.43	0.66/0.46	ns, Min
$T_{RDCK\_DI\_ECCW}/T_{RCKD\_DI\_ECCW}$	DIN inputs with block RAM ECC encode only[9]	0.79/0.37	0.87/0.39	0.99/0.43	1.17/0.41	ns, Min
$T_{RDCK\_DI\_ECC\_FIFO}/T_{RCKD\_DI\_ECC\_FIFO}$	DIN inputs with FIFO ECC in standard mode[9]	0.89/0.47	0.98/0.50	1.12/0.54	1.32/0.65	ns, Min
$T_{RCCK\_INJECTBITERR}/T_{RCKC\_INJECTBITERR}$	Inject single/double bit error in ECC mode	0.49/0.30	0.55/0.31	0.63/0.34	0.78/0.41	ns, Min
T_{RCCK_EN}/T_{RCKC_EN}	Block RAM Enable (EN) input	0.30/0.17	0.33/0.18	0.38/0.20	0.48/0.22	ns, Min
$T_{RCCK\_REGCE}/T_{RCKC\_REGCE}$	CE input of output register	0.21/0.13	0.25/0.13	0.31/0.14	0.34/0.16	ns, Min
$T_{RCCK\_RSTREG}/T_{RCKC\_RSTREG}$	Synchronous RSTREG input	0.25/0.06	0.27/0.06	0.29/0.06	0.35/0.06	ns, Min

Clock Buffers and Networks

Table 33: **Global Clock Switching Characteristics (Including BUFGCTRL)**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
$T_{BCCCK\_CE}/T_{BCCKC\_CE}$(1)	CE pins Setup/Hold	0.12/0.30	0.14/0.38	0.26/0.38	0.23/0.40	ns
T_{BCCCK_S}/T_{BCCKC_S}(1)	S pins Setup/Hold	0.12/0.30	0.14/0.38	0.26/0.38	0.23/0.40	ns
T_{BCCKO_O}(2)	BUFGCTRL delay from I0/I1 to O	0.08	0.10	0.12	0.10	ns
Maximum Frequency						
F_{MAX_BUFG}	Global clock tree (BUFG)	741.00	710.00	625.00	560.00	MHz

Notes:

1. T_{BCCCK_CE} and T_{BCCKC_CE} must be satisfied to assure glitch-free operation of the global clock when switching between clocks. These parameters do not apply to the BUFGMUX primitive that assures glitch-free operation. The other global clock setup and hold times are optional; only needing to be satisfied if device operation requires simulation matches on a cycle-for-cycle basis when switching between clocks.
2. T_{BGCKO_O} (BUFG delay from I0 to O) values are the same as T_{BCCKO_O} values.

Table 34: **Input/Output Clock Switching Characteristics (BUFIO)**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
T_{BIOCKO_O}	Clock to out delay from I to O	1.04	1.14	1.32	1.48	ns
Maximum Frequency						
F_{MAX_BUFIO}	I/O clock tree (BUFIO)	800.00	800.00	710.00	710.00	MHz

Table 35: **Regional Clock Buffer Switching Characteristics (BUFR)**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
T_{BRCKO_O}	Clock to out delay from I to O	0.60	0.65	0.77	1.06	ns
$T_{BRCKO\_O\_BYP}$	Clock to out delay from I to O with Divide Bypass attribute set	0.30	0.32	0.38	0.57	ns
T_{BRDO_O}	Propagation delay from CLR to O	0.71	0.75	0.96	0.93	ns
Maximum Frequency						
F_{MAX_BUFR}(1)	Regional clock tree (BUFR)	600.00	540.00	450.00	450.00	MHz

Notes:

1. The maximum input frequency to the BUFR is the BUFIO F_{MAX} frequency.

Table 42: **Clock-Capable Clock Input to Output Delay With MMCM**

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *with* MMCM.							
$T_{ICKOFMMCMCC}$	Clock-capable clock input and OUTFF *with* MMCM	XC7K70T	0.95	0.95	0.95	1.74	ns
		XC7K160T	0.96	0.96	0.96	1.78	ns
		XC7K325T	1.00	1.00	1.00	1.82	ns
		XC7K355T	1.00	1.00	1.00	1.78	ns
		XC7K410T	1.00	1.00	1.00	1.82	ns
		XC7K420T	1.07	1.07	1.07	1.82	ns
		XC7K480T	1.07	1.07	1.07	1.82	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. MMCM output jitter is already included in the timing calculation.

Table 43: **Clock-Capable Clock Input to Output Delay With PLL**

Symbol	Description	Device	Speed Grade				Units
			1.0V			0.9V	
			-3	-2/-2L	-1	-2L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *with* PLL.							
$T_{ICKOFPLLCC}$	Clock-capable clock input and OUTFF *with* PLL	XC7K70T	0.84	0.84	0.84	1.45	ns
		XC7K160T	0.89	0.89	0.89	1.54	ns
		XC7K325T	0.89	0.89	0.89	1.54	ns
		XC7K355T	0.89	0.89	0.89	1.50	ns
		XC7K410T	0.89	0.89	0.89	1.54	ns
		XC7K420T	0.96	0.96	0.96	1.54	ns
		XC7K480T	0.96	0.96	0.96	1.54	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. PLL output jitter is already included in the timing calculation.

Table 44: **Pin-to-Pin, Clock-to-Out using BUFIO**

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *with* BUFIO.						
$T_{ICKOFCS}$	Clock-to-Out of I/O clock for HR I/O banks	4.93	5.52	6.20	6.97	ns
	Clock-to-Out of I/O clock for HP I/O banks	4.85	5.44	6.11	6.90	ns

GTX Transceiver Specifications

GTX Transceiver DC Input and Output Levels

Table 51 summarizes the DC output specifications of the GTX transceivers in Kintex-7 FPGAs. Consult UG476: *7 Series FPGAs GTX/GTH Transceiver User Guide* for further details.

Table 51: **GTX Transceiver DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
DV_{PPOUT}	Differential peak-to-peak output voltage(1)	Transmitter output swing is set to maximum setting	–	–	1000	mV
$V_{CMOUTDC}$	DC common mode output voltage.	Equation based	$V_{MGTAVTT} - DV_{PPOUT}/4$			mV
R_{OUT}	Differential output resistance		–	100	–	Ω
T_{OSKEW}	Transmitter output pair (TXP and TXN) intra-pair skew		–	2	12	ps
DV_{PPIN}	Differential peak-to-peak input voltage (external AC coupled)	>10.3125 Gb/s	150	–	1250	mV
		6.6 Gb/s to 10.3125 Gb/s	150	–	1250	mV
		≤ 6.6 Gb/s	150	–	2000	mV
V_{IN}	Absolute input voltage	DC coupled $V_{MGTAVTT}$ = 1.2V	–200	–	$V_{MGTAVTT}$	mV
V_{CMIN}	Common mode input voltage	DC coupled $V_{MGTAVTT}$ = 1.2V	–	2/3 $V_{MGTAVTT}$	–	mV
R_{IN}	Differential input resistance		–	100	–	Ω
C_{EXT}	Recommended external AC coupling capacitor(2)		–	100	–	nF

Notes:

1. The output swing and preemphasis levels are programmable using the attributes discussed in UG476: *7 Series FPGAs GTX/GTH Transceiver User Guide* and can result in values lower than reported in this table.
2. Other values can be used as appropriate to conform to specific protocols and standards.

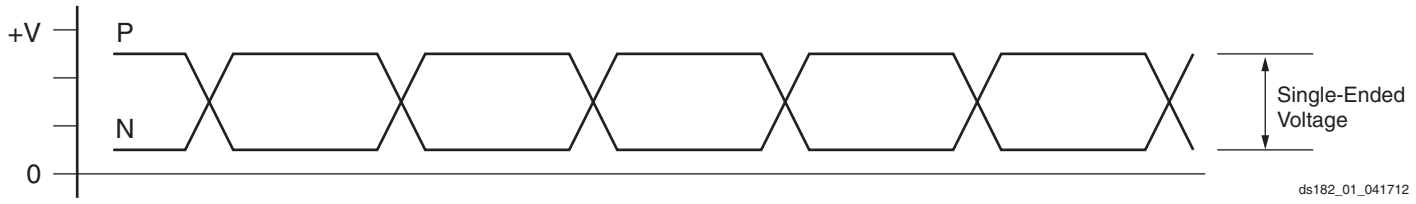

Figure 1: **Single-Ended Peak-to-Peak Voltage**

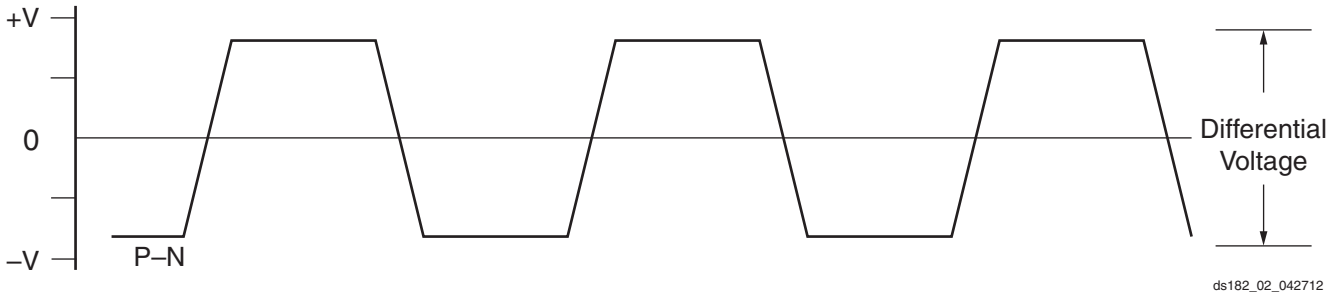

Figure 2: **Differential Peak-to-Peak Voltage**

Table 58: **GTX Transceiver Transmitter Switching Characteristics *(Cont'd)***

Symbol	Description	Condition	Min	Typ	Max	Units
$TJ_{10.3125}$	Total Jitter(2)(4)	10.3125 Gb/s	–	–	0.28	UI
$DJ_{10.3125}$	Deterministic Jitter(2)(4)		–	–	0.17	UI
$TJ_{9.953}$	Total Jitter(2)(4)	9.953 Gb/s	–	–	0.28	UI
$DJ_{9.953}$	Deterministic Jitter(2)(4)		–	–	0.17	UI
$TJ_{9.8}$	Total Jitter(2)(4)	9.8 Gb/s	–	–	0.28	UI
$DJ_{9.8}$	Deterministic Jitter(2)(4)		–	–	0.17	UI
$TJ_{8.0}$	Total Jitter(2)(4)	8.0 Gb/s	–	–	0.30	UI
$DJ_{8.0}$	Deterministic Jitter(2)(4)		–	–	0.15	UI
$TJ_{6.6\_QPLL}$	Total Jitter(2)(4)	6.6 Gb/s	–	–	0.28	UI
$DJ_{6.6\_QPLL}$	Deterministic Jitter(2)(4)		–	–	0.17	UI
$TJ_{6.6\_CPLL}$	Total Jitter(3)(4)	6.6 Gb/s	–	–	0.30	UI
$DJ_{6.6\_CPLL}$	Deterministic Jitter(3)(4)		–	–	0.15	UI
$TJ_{5.0}$	Total Jitter(3)(4)	5.0 Gb/s	–	–	0.30	UI
$DJ_{5.0}$	Deterministic Jitter(3)(4)		–	–	0.15	UI
$TJ_{4.25}$	Total Jitter(3)(4)	4.25 Gb/s	–	–	0.30	UI
$DJ_{4.25}$	Deterministic Jitter(3)(4)		–	–	0.15	UI
$TJ_{3.75}$	Total Jitter(3)(4)	3.75 Gb/s	–	–	0.30	UI
$DJ_{3.75}$	Deterministic Jitter(3)(4)		–	–	0.15	UI
$TJ_{3.2}$	Total Jitter(3)(4)	3.20 Gb/s(5)	–	–	0.2	UI
$DJ_{3.2}$	Deterministic Jitter(3)(4)		–	–	0.1	UI
$TJ_{3.2L}$	Total Jitter(3)(4)	3.20 Gb/s(6)	–	–	0.32	UI
$DJ_{3.2L}$	Deterministic Jitter(3)(4)		–	–	0.16	UI
$TJ_{2.5}$	Total Jitter(3)(4)	2.5 Gb/s(7)	–	–	0.20	UI
$DJ_{2.5}$	Deterministic Jitter(3)(4)		–	–	0.08	UI
$TJ_{1.25}$	Total Jitter(3)(4)	1.25 Gb/s(8)	–	–	0.15	UI
$DJ_{1.25}$	Deterministic Jitter(3)(4)		–	–	0.06	UI
TJ_{500}	Total Jitter(3)(4)	500 Mb/s	–	–	0.1	UI
DJ_{500}	Deterministic Jitter(3)(4)		–	–	0.03	UI

Notes:

1. Using same REFCLK input with TX phase alignment enabled for up to 12 consecutive transmitters (three fully populated GTX Quads).
2. Using QPLL_FBDIV = 40, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
3. Using CPLL_FBDIV = 2, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
4. All jitter values are based on a bit-error ratio of $1e^{-12}$.
5. CPLL frequency at 3.2 GHz and TXOUT_DIV = 2.
6. CPLL frequency at 1.6 GHz and TXOUT_DIV = 1.
7. CPLL frequency at 2.5 GHz and TXOUT_DIV = 2.
8. CPLL frequency at 2.5 GHz and TXOUT_DIV = 4.

GTX Transceiver Protocol Jitter Characteristics

For Table 60 through Table 65, the UG476: *7 Series FPGAs GTX/GTH Transceiver User Guide* contains recommended settings for optimal usage of protocol specific characteristics.

Table 60: **Gigabit Ethernet Protocol Characteristics**

Description	Line Rate (Mb/s)	Min	Max	Units
Gigabit Ethernet Transmitter Jitter Generation				
Total transmitter jitter (T_TJ)	1250	–	0.24	UI
Gigabit Ethernet Receiver High Frequency Jitter Tolerance				
Total receiver jitter tolerance	1250	0.749	–	UI

Table 61: **XAUI Protocol Characteristics**

Description	Line Rate (Mb/s)	Min	Max	Units
XAUI Transmitter Jitter Generation				
Total transmitter jitter (T_TJ)	3125	–	0.35	UI
XAUI Receiver High Frequency Jitter Tolerance				
Total receiver jitter tolerance	3125	0.65	–	UI

Table 62: **PCI Express Protocol Characteristics(1)**

Standard	Description		Line Rate (Mb/s)	Min	Max	Units
PCI Express Transmitter Jitter Generation						
PCI Express Gen 1	Total transmitter jitter		2500	–	0.25	UI
PCI Express Gen 2	Total transmitter jitter		5000	–	0.25	UI
PCI Express Gen 3(2)	Total transmitter jitter uncorrelated		8000	–	31.25	ps
	Deterministic transmitter jitter uncorrelated			–	12	ps
PCI Express Receiver High Frequency Jitter Tolerance						
PCI Express Gen 1	Total receiver jitter tolerance		2500	0.65	–	UI
PCI Express Gen 2(3)	Receiver inherent timing error		5000	0.40	–	UI
	Receiver inherent deterministic timing error			0.30	–	UI
PCI Express Gen 3(2)	Receiver sinusoidal jitter tolerance	0.03 MHz–1.0 MHz	8000	1.00	–	UI
		1.0 MHz–10 MHz		Note 4	–	UI
		10 MHz–100 MHz		0.10	–	UI

Notes:

1. Tested per card electromechanical (CEM) methodology.
2. PCI-SIG 3.0 certification and compliance test boards are currently not available.
3. Using common REFCLK.
4. Between 1 MHz and 10 MHz the minimum sinusoidal jitter roll-off with a slope of 20dB/decade.

XADC Specifications

Table 67: **XADC Specifications**

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
V_{CCADC} = 1.8V ± 5%, V_{REFP} = 1.25V, V_{REFN} = 0V, ADCCLK = 26 MHz, T_j = –40°C to 100°C, Typical values at T_j=+40°C						
ADC Accuracy(1)						
Resolution			12	–	–	Bits
Integral Nonlinearity(2)	INL		–	–	±3	LSBs
Differential Nonlinearity	DNL	No missing codes, guaranteed monotonic	–	–	±1	LSBs
Offset Error		Offset calibration enabled	–	–	±6	LSBs
Gain Error		Gain calibration disabled	–	–	±0.5	%
Offset Matching		Offset calibration enabled	–	–	4	LSBs
Gain Matching		Gain calibration disabled	–	–	0.3	%
Sample Rate			0.1	–	1	MS/s
Signal to Noise Ratio(2)	SNR	F_{SAMPLE} = 500KS/s, F_{IN} = 20KHz	60	–	–	dB
RMS Code Noise		External 1.25V reference	–	–	2	LSBs
		On-chip reference	–	3	–	LSBs
Total Harmonic Distortion(2)	THD	F_{SAMPLE} = 500KS/s, F_{IN} = 20KHz	–	70	–	dB
ADC Accuracy at Extended Temperatures (-55°C to 125°C)						
Resolution			10	–	–	Bits
Integral Nonlinearity(2)	INL		–	–	±1	LSB (at 10 bits)
Differential Nonlinearity	DNL	No missing codes, guaranteed monotonic	–	–	±1	
Analog Inputs(3)						
ADC Input Ranges		Unipolar operation	0	–	1	V
		Bipolar operation	–0.5	–	+0.5	V
		Unipolar common mode range (FS input)	0	–	+0.5	V
		Bipolar common mode range (FS input)	+0.5	–	+0.6	V
Maximum External Channel Input Ranges		Adjacent channels set within these ranges should not corrupt measurements on adjacent channels	–0.1	–	V_{CCADC}	V
Auxiliary Channel Full Resolution Bandwidth	FRBW		250	–	–	KHz
On-Chip Sensors						
Temperature Sensor Error		T_j = –40°C to 100°C.	–	–	±4	°C
		T_j = –55°C to +125°C	–	–	±6	°C
Supply Sensor Error		Measurement range of V_{CCAUX} 1.8V ±5% T_j = –40°C to +100°C	–	–	±1	%
		Measurement range of V_{CCAUX} 1.8V ±5% T_j = –55°C to +125°C	–	–	±2	%
Conversion Rate(4)						
Conversion Time - Continuous	t_{CONV}	Number of ADCCLK cycles	26	–	32	Cycles
Conversion Time - Event	t_{CONV}	Number of CLK cycles	–	–	21	Cycles
DRP Clock Frequency	DCLK	DRP clock frequency	8	–	250	MHz
ADC Clock Frequency	ADCCLK	Derived from DCLK	1	–	26	MHz
DCLK Duty Cycle			40	–	60	%

Table 68: **Configuration Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade				Units
		1.0V			0.9V	
		-3	-2/-2L	-1	-2L	
Master/Slave Serial Mode Programming Switching						
T_{DCCK}/T_{CCKD}	DIN Setup/Hold	4.00/0.00	4.00/0.00	4.00/0.00	5.00/0.00	ns, Min
T_{CCO}	DOUT clock to out	8.00	8.00	8.00	9.00	ns, Max
SelectMAP Mode Programming Switching						
T_{SMDCCK}/T_{SMCCKD}	D[31:00] Setup/Hold	4.00/0.00	4.00/0.00	4.00/0.00	4.50/0.00	ns, Min
$T_{SMCSCCK}/T_{SMCCKCS}$	CSI_B Setup/Hold	4.00/0.00	4.00/0.00	4.00/0.00	5.00/0.00	ns, Min
T_{SMWCCK}/T_{SMCCKW}	RDWR_B Setup/Hold	10.00/0.00	10.00/0.00	10.00/0.00	12.00/0.00	ns, Min
$T_{SMCKCSO}$	CSO_B clock to out (330 Ω pull-up resistor required)	7.00	7.00	7.00	8.00	ns, Max
T_{SMCO}	D[31:00] clock to out in readback	8.00	8.00	8.00	10.00	ns, Max
F_{RBCCK}	Readback frequency	100.00	100.00	100.00	70.00	MHz, Max
Boundary-Scan Port Timing Specifications						
T_{TAPTCK}/T_{TCKTAP}	TMS and TDI Setup/Hold	3.00/2.00	3.00/2.00	3.00/2.00	3.00/2.00	ns, Min
T_{TCKTDO}	TCK falling edge to TDO output	7.00	7.00	7.00	8.50	ns, Max
F_{TCK}	TCK frequency	66.00	66.00	66.00	50.00	MHz, Max
BPI Master Flash Mode Programming Switching						
T_{BPICCO}(2)	A[28:00], RS[1:0], FCS_B, FOE_B, FWE_B, ADV_B clock to out	8.50	8.50	8.50	10.00	ns, Max
T_{BPIDCC}/T_{BPICCD}	D[15:00] Setup/Hold	4.00/0.00	4.00/0.00	4.00/0.00	4.50/0.00	ns, Min
SPI Master Flash Mode Programming Switching						
T_{SPIDCC}/T_{SPICCD}	D[03:00] Setup/Hold	3.00/0.00	3.00/0.00	3.00/0.00	3.00/0.00	ns, Min
T_{SPICCM}	MOSI clock to out	8.00	8.00	8.00	9.00	ns, Max
$T_{SPICCFC}$	FCS_B clock to out	8.00	8.00	8.00	9.00	ns, Max

Notes:

1. To support longer delays in configuration, use the design solutions described in UG470: *7 Series FPGA Configuration User Guide*.
2. Only during configuration, the last edge is determined by a weak pull-up/pull-down resistor in the I/O.

eFUSE Programming Conditions

Table 69 lists the programming conditions specifically for eFUSE. For more information, see UG470: *7 Series FPGA Configuration User Guide*.

Table 69: **eFUSE Programming Conditions(1)**

Symbol	Description	Min	Typ	Max	Units
I_{FS}	V_{CCAUX} supply current	–	–	115	mA
t_j	Temperature range	15	–	125	°C

Notes:

1. The FPGA must not be configured during eFUSE programming.

Notice of Disclaimer